

Field Effect Transistor

Silicon N Channel MOS Type (π -MOS II)

High Speed, High Current DC-DC Converter,

Relay Drive and Motor Drive Applications

Features

- 4-Volt Gate Drive
- Low Drain-Source ON Resistance
 - $R_{DS(ON)} = 0.040\Omega$ (Typ.)
- High Forward Transfer Admittance
 - $|Y_{fs}| = 11S$ (Typ.)
- Low Leakage Current
 - $I_{DSS} = 300\mu A$ (Max.) @ $V_{DS} = 60V$
- Enhancement-Mode
 - $V_{th} = 1.5 \sim 3.5V$ @ $V_{DS} = 10V$, $I_D = 1mA$

Absolute Maximum Ratings ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)		V_{DGR}	60	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	25	A
	Pulse	I_{DP}	100	
Drain Power Dissipation ($T_c = 25^\circ C$)		P_D	40	W
Channel Temperature		T_{ch}	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55 ~ 150	$^\circ C$

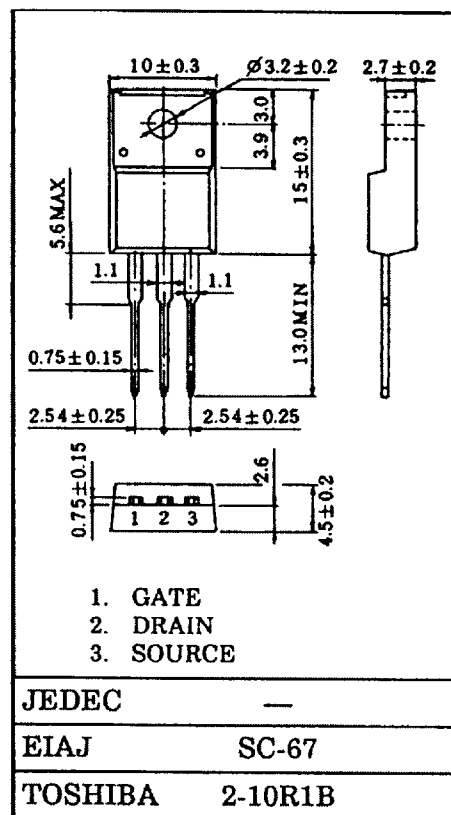
Thermal Characteristics

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	3.125	$^\circ C/W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	62.5	$^\circ C/W$

This transistor is an electrostatic sensitive device. Please handle with care.

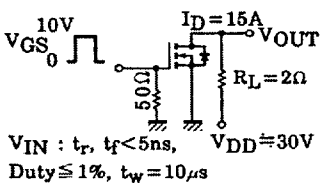
Industrial Applications

Unit in mm



Weight : 1.9g

Electrical Characteristics (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	—	—	± 100	nA
Drain Cut-off Current		I_{DSS}	$V_{DS} = 60V, V_{GS} = 0V$	—	—	300	μA
Drain-Source Breakdown Voltage		$V_{(BR) DSS}$	$I_D = 10mA, V_{GS} = 0V$	60	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = 10V, I_D = 1mA$	1.5	—	3.5	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$I_D = 15A, V_{GS} = 10V$	—	0.040	0.060	Ω
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 10V, I_D = 4A$	8.0	11	—	S
Input Capacitance		C_{iss}	$V_{DS} = 10V, V_{GS} = 0V,$ $f = 1MHz$	—	1200	1600	pF
Reverse Transfer Capacitance		C_{rss}		—	320	450	
Output Capacitance		C_{oss}		—	1200	1600	
Switching Time	Rise Time	t_r	 $V_{IN} : t_r, t_f < 5ns, V_{DD} = 30V$ $Duty \leq 1\%, t_w = 10\mu s$	—	80	160	ns
	Turn-on Time	t_{on}		—	100	200	
	Fall Time	t_f		—	85	170	
	Turn-off Time	t_{off}		—	165	330	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} = 48V, V_{GS} = 10V,$ $I_D = 25A$	—	38	60	nC
Gate-Source Charge		Q_{gs}		—	20	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	18	—	

Source-Drain Diode Ratings and Characteristics (Ta = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	25	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	100	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 25A, V_{GS} = 0V$	—	—	-1.7	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 25A, V_{GS} = 0V$	—	160	—	ns
Reverse Recovered Charge	Q_{rr}	$dI_{DR}/dt = 100A/\mu s$	—	0.6	—	μC

